

H5N2513PL

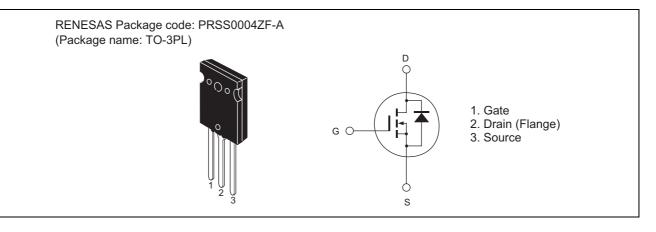
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1243-0100 Rev.1.00 Jul 25, 2008

Features

- Low on-resistance
- High speed switching
- www.DataSheet4U.Built-in fast recovery diode

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	Ι _D	100	A
Drain peak current	I _{D (pulse)} Note1	400	A
Body-drain diode reverse drain current	I _{DR}	100	A
Body-drain diode reverse drain	Note1 I _{DR (pulse)}	400	A
peak current			
Avalanche current	I _{AP} Note3	100	A
Avalanche energy	E _{AR} Note3	625	mJ
Channel dissipation	Pch Note2	250	W
Channel to case thermal impedance	θch-c	0.5	°C/W
Channel temperature	Tch	150	۵°
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

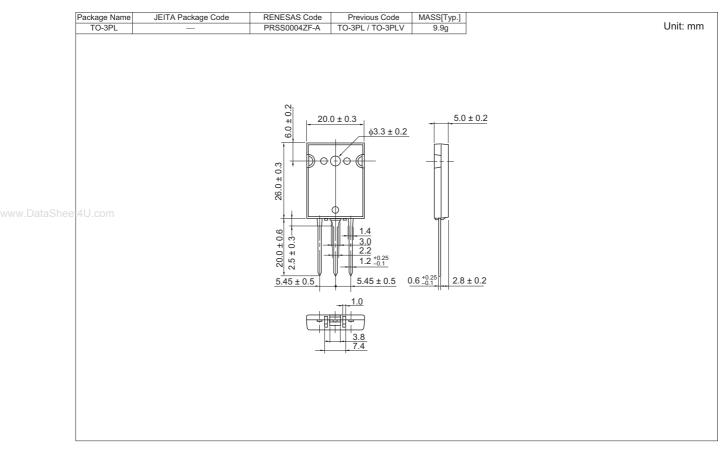
3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	V _{(BR)DSS}	250	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	10	μΑ	$V_{DS} = 250 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		—	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Forward transfer admittance	y _{fs}	39	65	_	S	$I_D = 50 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Static drain to source on state resistance	R _{DS(on)}	_	0.020	0.026	Ω	$I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	9300	-	pF	$V_{DS} = 25 \text{ V}, V_{GS} = 0,$ f = 1 MHz
Output capacitance	Coss		1200		pF	
Reverse transfer capacitance	Crss		280		pF	
Turn-on delay time	t _{d(on)}		90		ns	I_D = 50 A, V _{GS} = 10 V, R _L = 2.5 Ω, Rg = 10 Ω
Rise time	tr		420		ns	
Turn-off delay time	t _{d(off)}		550		ns	
Fall time	t _f		400		ns	
Total gate charge	Qg		330		nC	$V_{DD} = 200 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$ $I_D = 100 \text{ A}$
Gate to source charge	Qgs		45		nC	
Gate to drain charge	Qgd	_	175	—	nC	
Body-drain diode forward voltage	V _{DF}	_	1.2	1.8	V	$I_F = 100 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}	_	210	_	ns	I _F = 100 A, V _{GS} = 0 diF/dt = 100 A/μs

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N2513PL-E	100 pcs.	Plastic case

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